

15.45/6059

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of:) Group Art Unit: 2811
TAKEUCHI)
Serial No. 09/930,365) Examiner: Wu
Filed: June 19, 2001)
For: METHODS FOR MANUFACTURING)
SEMICONDUCTOR DEVICES AND)
SEMICONDUCTOR DEVICES HAVING)
TRENCH ISOLATION REGIONS)

#5
PreAmotta
FJONES
5-29-02

PRELIMINARY AMENDMENT

Assistant Commissioner for Patents
Washington, DC 20231

Dear Sir:

Please enter the following.

IN THE CLAIMS:

Please amend claim 26 as follows:

26. (amended) A method as in claim 19, wherein the dielectric layer is formed using high density plasma chemical vapor deposition.

Remarks

Claims 1-31 are pending. Applicant has amended claim 26 for clarity. Claim 26, as amended, depends from claim 19. Examination is respectfully requested.

Attached to this paper is a marked-up version of the changes to the claims made by the present amendment. The attached page is captioned "Version With Markings to Show Changes Made."